Abstracts

A general parameter extraction method for transistor noise models with correlation

J. Stenarson, M. Garcia, I. Angelov and H. Zirath. "A general parameter extraction method for transistor noise models with correlation." 1999 MTT-S International Microwave Symposium Digest 99.1 (1999 Vol. I [MWSYM]): 113-116 vol.1.

A new general direct extraction procedure for transistor noise models including two correlated noise sources is developed. The extraction procedure is demonstrated for a Silicon Carbide (SiC) Metal Semiconductor Field Effect Transistor (MESFET). The extracted model shows good agreement to measured noise parameters.

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